

PSMN1R1-30EL

N-channel 30 V 1.3 mΩ logic level MOSFET in I2PAK

2 April 2014 Product data sheet

1. General description

Logic level N-channel MOSFET in I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

3. Applications

- DC-to-DC converters
- Load switiching
- Motor control
- Server power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	338	W
Tj	junction temperature			-55	-	175	°C
Static charac	cteristics					'	
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12	[2]	-	1.1	1.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 ^{\circ}\text{C};$ Fig. 13		-	1.5	1.8	mΩ
Dynamic cha	aracteristics		'				-
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_{D} = 75 A; V_{DS} = 15 V;		-	37	-	nC
Q _{G(tot)}	total gate charge	Fig. 14; Fig. 15		-	118	-	nC



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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω; unclamped		-	-	1.9	J

- [1] Continuous current is limited by package.
- [2] Measured 3 mm from package.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain		
3	S	source		G—VIII
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			I2PAK (SOT226)	

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PSMN1R1-30EL	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226				

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R1-30EL	PSMN1R1-30EL

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
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Symbol	Parameter	Conditions		Min	Max	Unit
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	338	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	120	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	120	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3		-	1609	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	in diode					,
I _S	source current	T _{mb} = 25 °C	[1]	-	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1609	Α
Avalanche	ruggedness	,	1	'	'	
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω; unclamped		-	1.9	J

[1] Continuous current is limited by package.

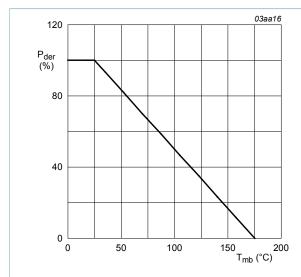


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\text{C})}} \times \textbf{100 \%}$$

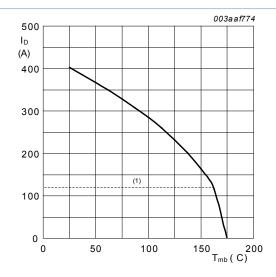


Fig. 2. Continuous drain current as a function of mounting base temperature.

 $V_{\it GS} \ge 10~{
m V};~~(1)~{
m Capped}$ at 120 A due to package

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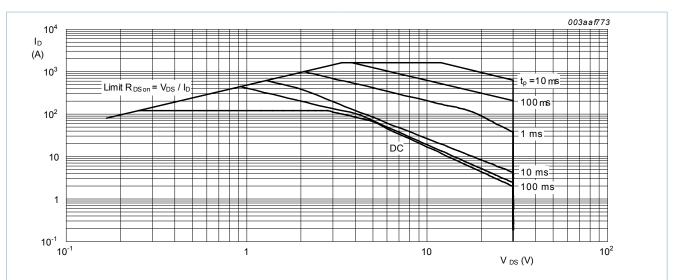


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 T_{mb} = 25 °C; I_{DM} is a single pulse; Capped at 120 A due to package

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.22	0.44	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

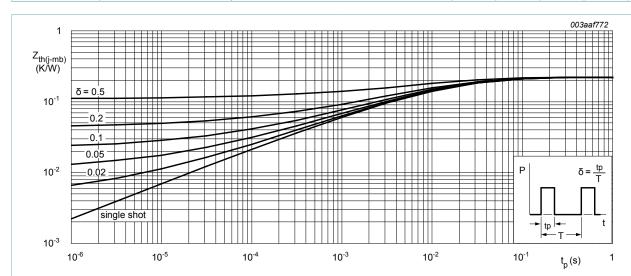


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Uni
Static chara	cteristics						
V _{(BR)DSS} drain-source breakdown voltage		I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		30	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C		27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11		1.3	1.7	2.15	V
		$I_D = 2 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 11		0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 11		-	-	2.5	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	0.02	10	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 175 °C		-	250	500	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C		-	10	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C		-	10	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 12	[1]	-	1.1	1.3	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; Fig. 12		-	1.2	1.6	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ Fig. 13; Fig. 12		-	2.1	2.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 ^{\circ}\text{C};$ Fig. 13		-	1.5	1.8	mΩ
R_G	gate resistance	f = 1 MHz		-	1.1		Ω
Dynamic cha	aracteristics						
Q _{G(tot)}	total gate charge	I _D = 75 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 14; Fig. 15		-	243	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V; Fig. 14; Fig. 15		-	222	-	nC
		I _D = 75 A; V _{DS} = 15 V; V _{GS} = 4.5 V;		-	118	-	nC
Q_{GS}	gate-source charge	Fig. 14; Fig. 15		-	39	-	nC
Q _{GS(th)}	pre-threshold gate- source charge			-	22	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge			-	17	-	nC
Q_{GD}	gate-drain charge			-	37	-	nC
V _{GS(pI)}	gate-source plateau voltage	V _{DS} = 15 V; <u>Fig. 14</u> ; <u>Fig. 15</u>		-	2.8	-	V

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$		-	14850	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>		-	2799	-	pF
C _{rss}	reverse transfer capacitance			-	1215	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_{L} = 0.2 Ω ; V_{GS} = 4.5 V; $R_{G(ext)}$ = 5 Ω ; I_{D} = 75 A; T_{j} = 25 °C		-	95	-	ns
t _r	rise time			-	213	-	ns
t _{d(off)}	turn-off delay time			-	199	-	ns
t _f	fall time			-	115	-	ns
Source-dra	ain diode		I				
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$		-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 15 \text{ V}$		-	67	-	ns
Q _r	recovered charge			-	123	-	nC

[1] Measured 3 mm from package.

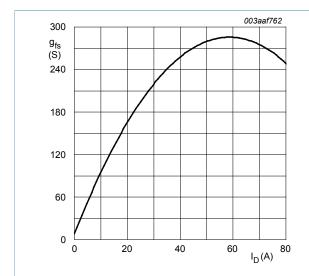


Fig. 5. Forward transconductance as a function of drain current; typical values

$$T_j=25\,^{\circ}C; V_{DS}=15\,V$$

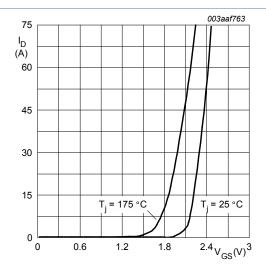


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} > I_D \times R_{DSon}$$

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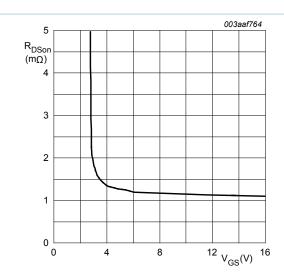


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25 \,^{\circ}C; I_D = 25A$$

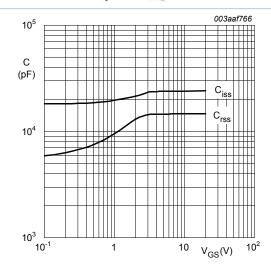


Fig. 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

$$V_{DS} = 0V; f = 1MHz$$

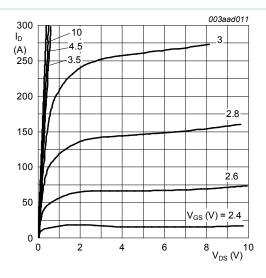


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25\,^{\circ}C$$

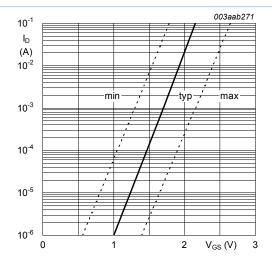


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
 °C; $V_{DS} = 5V$

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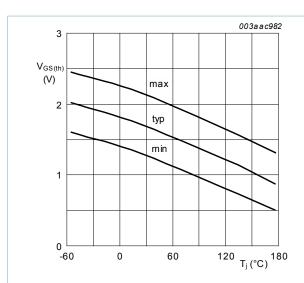
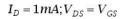


Fig. 11. Gate-source threshold voltage as a function of junction temperature



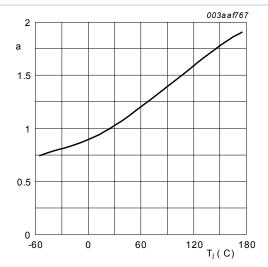


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

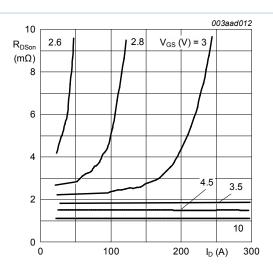


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

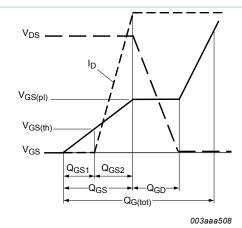


Fig. 14. Gate charge waveform definitions

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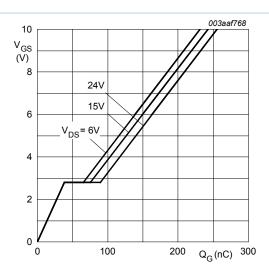


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
 °C; $I_D = 75$ A

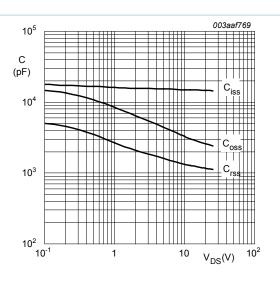


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

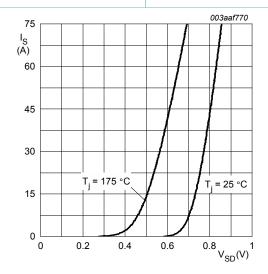


Fig. 17. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0 V$$

11. Package outline

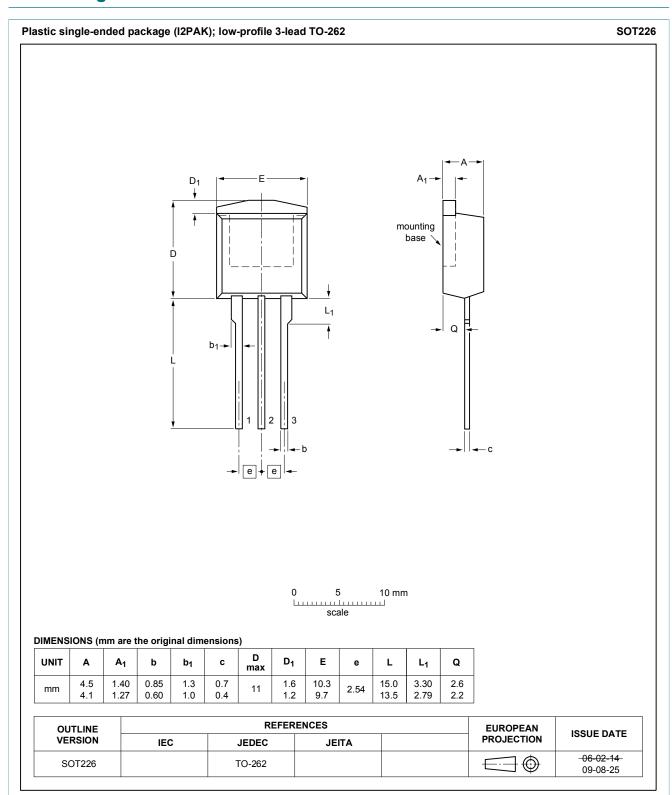


Fig. 18. Package outline I2PAK (SOT226)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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